AUTOMOTIVE

GREEN \*\*

(5-2008)<sup>1</sup>



# Vishay Semiconductors

# Infrared Emitting Diode, 950 nm, GaAs



### **DESCRIPTION**

VSMS3700 is an infrared, 950 nm emitting diode in GaAs technology, molded in a PLCC-2 package for surface mounting (SMD).

## **FEATURES**

· Package type: surface mount

• Package form: PLCC-2

• Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75

• Peak wavelength:  $\lambda_p = 950 \text{ nm}$ 

High reliability

• Angle of half intensity:  $\varphi = \pm 60^{\circ}$ 

• Low forward voltage

• Suitable for high pulse current operation

 Good spectral matching with Si photodetectors

• Package matched with IR emitter series VEMT3700

• Floor life: 168 h, MSL 3, acc. J-STD-020

• Lead (Pb)-free reflow soldering

AEC-Q101 qualified

• Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications

## **APPLICATIONS**

- Infrared source in tactile keyboards
- IR diode in low space applications
- · PCB mounted infrared sensors
- Emitter in miniature photo-interrupters

| PRODUCT SUMMARY |                        |         |                             |                     |
|-----------------|------------------------|---------|-----------------------------|---------------------|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (deg) | $\lambda_{\mathbf{P}}$ (nm) | t <sub>r</sub> (ns) |
| VSMS3700        | 4.5                    | ± 60    | 950                         | 800                 |

#### Note

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |               |                              |              |  |
|----------------------|---------------|------------------------------|--------------|--|
| ORDERING CODE        | PACKAGING     | REMARKS                      | PACKAGE FORM |  |
| VSMS3700-GS08        | Tape and reel | MOQ: 7500 pcs, 1500 pcs/reel | PLCC-2       |  |
| VSMS3700-GS18        | Tape and reel | MOQ: 8000 pcs, 8000 pcs/reel | PLCC-2       |  |

#### Note

MOQ: minimum order quantity

<sup>\*\*</sup> Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

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| ABSOLUTE MAXIMUM RATINGS            |                                |                   |               |      |  |
|-------------------------------------|--------------------------------|-------------------|---------------|------|--|
| PARAMETER                           | TEST CONDITION                 | SYMBOL            | VALUE         | UNIT |  |
| Reverse voltage                     |                                | V <sub>R</sub>    | 5             | V    |  |
| Forward current                     |                                | I <sub>F</sub>    | 100           | mA   |  |
| Peak forward current                | $t_p/T = 0.5, t_p = 100 \mu s$ | I <sub>FM</sub>   | 200           | mA   |  |
| Surge forward current               | t <sub>p</sub> = 100 μs        | I <sub>FSM</sub>  | 1.5           | Α    |  |
| Power dissipation                   |                                | P <sub>V</sub>    | 170           | mW   |  |
| Junction temperature                |                                | T <sub>j</sub>    | 100           | °C   |  |
| Operating temperature range         |                                | T <sub>amb</sub>  | - 40 to + 85  | °C   |  |
| Storage temperature range           |                                | T <sub>stg</sub>  | - 40 to + 100 | °C   |  |
| Soldering temperature               | Acc. figure 11, J-STD-020      | T <sub>sd</sub>   | 260           | °C   |  |
| Thermal resistance junction/ambient | J-STD-051, soldered on PCB     | R <sub>thJA</sub> | 250           | K/W  |  |

## Note

 $T_{amb}$  = 25 °C, unless otherwise specified

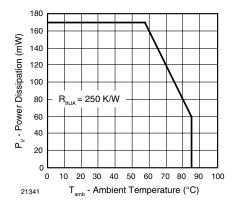


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

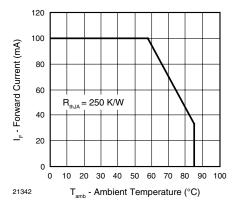


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS                     |   |                  |      |       |      |       |
|---|---|------------------|------|-------|------|-------|
| PARAMETER                                 | TEST CONDITION                                | SYMBOL           | MIN. | TYP.  | MAX. | UNIT  |
| Forward voltage                           | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$   | V <sub>F</sub>   |      | 1.3   | 1.7  | V     |
|   | $I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$   | V <sub>F</sub>   |      | 1.8   |      | V     |
| Temperature coefficient of V <sub>F</sub> | I <sub>F</sub> = 100 mA                       | TK <sub>VF</sub> |      | - 1.3 |      | mV/K  |
| Reverse current                           | V <sub>R</sub> = 5 V                          | I <sub>R</sub>   |      |       | 100  | μΑ    |
| Junction capacitance                      | V <sub>R</sub> = 0 V, f = 1 MHz, E = 0        | Cj               |      | 30    |      | pF    |
| Radiant intensity                         | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$   | l <sub>e</sub>   | 1.6  | 4.5   | 8    | mW/sr |
|   | $I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$ | I <sub>e</sub>   |      | 35    |      | mW/sr |
| Radiant power                             | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$   | фe               |      | 15    |      | mW    |
| Temperature coefficient of φ <sub>e</sub> | I <sub>F</sub> = 100 mA                       | TKφ <sub>e</sub> |      | - 0.8 |      | %/K   |
| Angle of half intensity                   |   | φ                |      | ± 60  |      | deg   |
| Peak wavelength                           | I <sub>F</sub> = 100 mA                       | $\lambda_{p}$    |      | 950   |      | nm    |
| Spectral bandwidth                        | I <sub>F</sub> = 100 mA                       | Δλ               |      | 50    |      | nm    |
| Temperature coefficient of $\lambda_p$    | I <sub>F</sub> = 100 mA                       | TKλ <sub>p</sub> |      | 0.2   |      | nm/K  |
| Rise time                                 | I <sub>F</sub> = 20 mA                        | t <sub>r</sub>   |      | 800   |      | ns    |
|   | I <sub>F</sub> = 1 A                          | t <sub>r</sub>   |      | 400   |      | ns    |
| Fall time                                 | I <sub>F</sub> = 20 mA                        | t <sub>f</sub>   |      | 800   |      | ns    |
|   | I <sub>F</sub> = 1 A                          | t <sub>f</sub>   |      | 400   |      | ns    |
| Virtual source diameter                   | EN 60825-1                                    | d                |      | 0.5   |      | mm    |

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified



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## **BASIC CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified

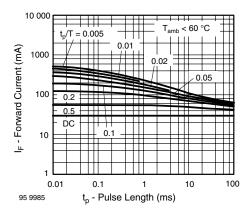


Fig. 3 - Pulse Forward Current vs. Pulse Duration

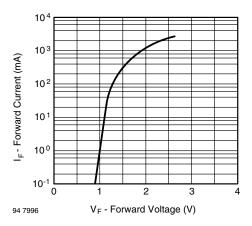


Fig. 4 - Forward Current vs. Forward Voltage

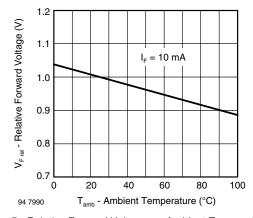


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

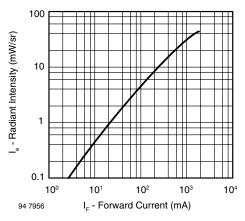


Fig. 6 - Radiant Intensity vs. Forward Current

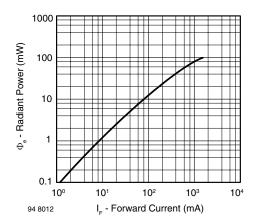


Fig. 7 - Radiant Power vs. Forward Current

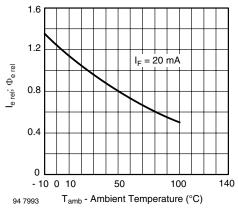


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

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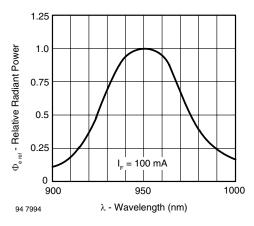


Fig. 9 - Relative Radiant Power vs. Wavelength

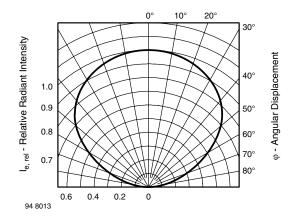
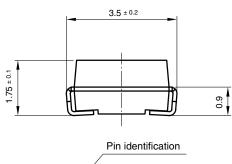
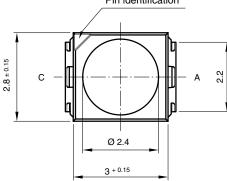


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

## **PACKAGE DIMENSIONS** in millimeters

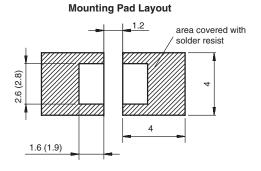




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# Die Position (for reference only)

X = +/- 0.2 mm centrical

Y = +/- 0.2 mm centrical

Z = 1.13 mm + /- 0.25 mm, from top of die bottom of component



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## **SOLDER PROFILE**

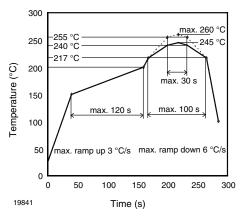


Fig. 11 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

### **DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

### **FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

Conditions:  $T_{amb} < 30$  °C, RH < 60~%

Moisture sensitivity level 3, acc. to J-STD-020.

### **DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40  $^{\circ}$ C (+ 5  $^{\circ}$ C), RH < 5  $^{\circ}$ M.

### **TAPE AND REEL**

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

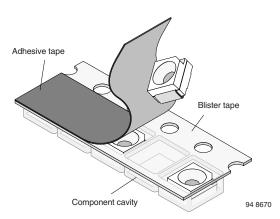


Fig. 12 - Blister Tape

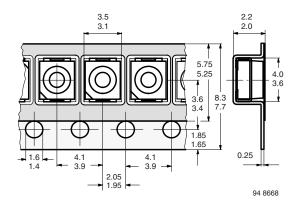


Fig. 13 - Tape Dimensions in mm for PLCC-2

### **MISSING DEVICES**

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

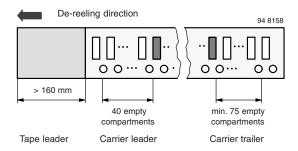


Fig. 14 - Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartments and sealed with cover tape.

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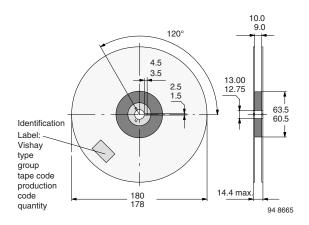


Fig. 15 - Dimensions of Reel-GS08

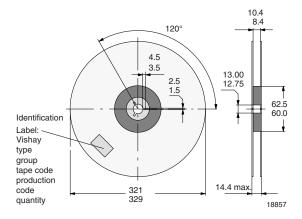


Fig. 16 - Dimensions of Reel-GS18

## **COVER TAPE REMOVAL FORCE**

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



# **Legal Disclaimer Notice**

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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